

Jinyoung Hwang

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Electrical Performance of Amorphous Oxide/Colloidal Quantum Dot/Amorphous Oxide Hybrid Thin Film Transistor. Transactions on Electrical and Electronic Materials, 2022, 23, 25.	1.9	0
2	Ammonia Gas Sensing Properties of 6,13-Bis(tri-isopropylsilyl)ethynyl Pentacene Based Field-Effect Transistor. Transactions on Electrical and Electronic Materials, 2022, 23, 182-186.	1.9	3
3	Investigation of the Stability and the Transparency of Oxide Thin Film Transistor with bi-Layer Channels and Oxide/Metal/Oxide Multilayer Source/Drain Electrodes. Transactions on Electrical and Electronic Materials, 2022, 23, 187-192.	1.9	0
4	Effect of Silicon Doping on the Electrical Performance of Amorphous SiInZnO Thin-film Transistors. Transactions on Electrical and Electronic Materials, 2021, 22, 133-139.	1.9	1
5	Influence of Si ²⁺ In ²⁺ Zn ²⁺ O/Ag/Si ²⁺ In ²⁺ Zn ²⁺ O Electrode on Amorphous Si ²⁺ Zn ²⁺ Sn ²⁺ O Thin Film Transistors. Transactions on Electrical and Electronic Materials, 2021, 22, 103-107.	1.9	2
6	High Sensitivity of HCl Gas Sensor Based on Pentacene Organic Field-Effect Transistor. Transactions on Electrical and Electronic Materials, 2021, 22, 140-145.	1.9	3
7	Optimization of transparent amorphous oxide-metal-amorphous oxide multilayer with high figure of merit for high transmittance and low resistivity. Optical Materials, 2021, 112, 110820.	3.6	5
8	Derivation of Dielectric Constant and Debye Length of Amorphous Si ²⁺ In ²⁺ Zn ²⁺ O by Analyzing Optical Coefficients. Transactions on Electrical and Electronic Materials, 2021, 22, 378-381.	1.9	1
9	Investigation on the Relaxation Time Response of Metal Capped Amorphous Oxide Si ²⁺ In ²⁺ Zn ²⁺ O Thin Film Transistors. Transactions on Electrical and Electronic Materials, 2021, 22, 419-423.	1.9	0
10	Layer Thickness Dependency of Oxide ²⁺ Metal ²⁺ Oxide Electrode on the Electrical Performance of Oxide Thin Film Transistors. Transactions on Electrical and Electronic Materials, 2021, 22, 593-597.	1.9	1
11	Realization of Inverter and Logic Circuit Using Amorphous Si ²⁺ In ²⁺ Zn ²⁺ O Thin Film Transistor. Transactions on Electrical and Electronic Materials, 2021, 22, 598-602.	1.9	1
12	Mechanism of Extraordinary High Mobility in Multilayered Amorphous Oxide Thin Film Transistor. IEEE Transactions on Electron Devices, 2021, 68, 5618-5622.	3.0	5
13	Electrical and Optical Properties of Flexible SiInZnO/Ag/SiInZnO Multilayer Electrodes. Transactions on Electrical and Electronic Materials, 2020, 21, 117-122.	1.9	4
14	Transmission Line Method Analysis on the Electrical Properties of Bi-Layer Channel Oxide Thin Film Transistors with Oxide-Metal-Oxide Electrodes. Transactions on Electrical and Electronic Materials, 2020, 21, 612-616.	1.9	2
15	Effect of Carrier Diffusion on the Optical Property in Si ²⁺ In ²⁺ Zn ²⁺ O/Ag/Si ²⁺ In ²⁺ Zn ²⁺ O Optical Media. Transactions on Electrical and Electronic Materials, 2020, 21, 599-605.	1.9	0
16	Carrier concentration dependency of plasma frequency in SiInZnO/Ag/SiInZnO transparent multilayer. Physica B: Condensed Matter, 2020, 592, 412242.	2.7	4
17	Effect of channel thickness on the electrical performance and the stability of amorphous SiZnSnO thin film transistor. Materials Science in Semiconductor Processing, 2020, 117, 105183.	4.0	8
18	Optimized Design of SiInZnO/Ag/SiInZnO Transparent Conductive Electrode by Using Optical Admittance Simulation. Transactions on Electrical and Electronic Materials, 2020, 21, 324-328.	1.9	1

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19	Comprehensive Review on Amorphous Oxide Semiconductor Thin Film Transistor. Transactions on Electrical and Electronic Materials, 2020, 21, 235-248.	1.9	43
20	Ag Layer Thickness Dependency of Electrical and Optical Properties of SiZnSnO/Ag/SiZnSnO Multilayer for High Performance and In-Free Transparent Conducting Electrode. Transactions on Electrical and Electronic Materials, 2019, 20, 417-419.	1.9	3
21	Amorphous Si _{1-x} Zn _x Sn _{1-x} O Thin Film Transistor with In _{1-x} Si _x O as Transparent Conducting Electrodes. Transactions on Electrical and Electronic Materials, 2019, 20, 371-374.	1.9	0
22	Effect of Carrier Diffusion on Optical Bandgap Design of Metal Oxide/Metal/Metal Oxide Multilayer. Transactions on Electrical and Electronic Materials, 2019, 20, 564-568.	1.9	2
23	Effect of RF Sputtering Power on the Electrical Properties of Si _{1-x} In _x Zn _{1-x} O Thin Film Transistors. Transactions on Electrical and Electronic Materials, 2019, 20, 518-521.	1.9	1
24	High Performance of Cost-Effective Low-E Coating on Flexible PET Substrate with Transparent Amorphous Oxide Semiconductor. Transactions on Electrical and Electronic Materials, 2019, 20, 554-557.	1.9	2
25	Mechanism of carrier controllability with metal capping layer on amorphous oxide SiZnSnO semiconductor. Scientific Reports, 2019, 9, 886.	3.3	22
26	Effect of Nitrogen Doping on the Electrical Performance of Amorphous Si _{1-x} In _x Zn _{1-x} O Thin Film Inverter. Transactions on Electrical and Electronic Materials, 2019, 20, 12-15.	1.9	4
27	Simulation and optimization of layer thickness of amorphous oxide SIZO/Ag/SIZO multilayer to enhance transmittance of transparent electrodes without sacrificing sheet resistance. Journal of Alloys and Compounds, 2019, 798, 622-627.	5.5	8
28	Dependency of Si Content on the Performance of Amorphous SiZnSnO Thin Film Transistor Based Logic Circuits for Next-Generation Integrated Circuits. Transactions on Electrical and Electronic Materials, 2019, 20, 175-180.	1.9	6
29	Investigation on energy bandgap states of amorphous SiZnSnO thin films. Scientific Reports, 2019, 9, 19246.	3.3	15
30	Development of Amorphous SIZO/Ag/Amorphous SIZO Multilayer for High-Performance Transparent Conducting Electrode by Controlling Ag Layer Thickness. Journal of Nanoscience and Nanotechnology, 2019, 19, 1755-1758.	0.9	1
31	Thin Film Logic Circuits with Amorphous SiInZnO Channel Layer Annealed at Different Atmospheres for Next-Generation Integrated Circuits. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700732.	1.8	3
32	Investigation on the variation of channel resistance and contact resistance of SiZnSnO semiconductor depending on Si contents using transmission line method. Solid-State Electronics, 2018, 139, 15-20.	1.4	5
33	Optical and Electrical Properties of Highly Transparent In _{1-x} Zn _x O/Ag/In _{1-x} Zn _x O Multilayers Deposited At Room Temperature. Transactions on Electrical and Electronic Materials, 2018, 19, 212-214.	1.9	3
34	Influence of Channel Layer Thickness on the Instability of Amorphous SiZnSnO Thin Film Transistors Under Negative Bias Temperature Stress. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700698.	1.8	15
35	Low-Temperature-Processed SiInZnO Thin-Film Transistor Fabricated by Radio Frequency Magnetron Sputtering. Transactions on Electrical and Electronic Materials, 2018, 19, 218-221.	1.9	3
36	Direct investigation on energy bandgap of Si added ZnSnO system for stability enhancement by X-ray photoelectron spectroscopy. Journal of Alloys and Compounds, 2017, 715, 9-15.	5.5	22

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37	Color-selective photodetection from intermediate colloidal quantum dots buried in amorphous-oxide semiconductors. <i>Nature Communications</i> , 2017, 8, 840.	12.8	47
38	Effect of Si on the Energy Band Gap Modulation and Performance of Silicon Indium Zinc Oxide Thin-Film Transistors. <i>Scientific Reports</i> , 2017, 7, 15392.	3.3	29
39	Metal Capping on Silicon Indium Zinc Oxide Semiconductor for High Performance Thin Film Transistors Processed at 150 Å°C. <i>Journal of Nanoscience and Nanotechnology</i> , 2017, 17, 3397-3400.	0.9	6
40	Low Emissivity Property of Amorphous Oxide Multilayer (SIZO/Ag/SIZO) Structure. <i>Transactions on Electrical and Electronic Materials</i> , 2017, 18, 13-15.	1.9	8
41	Influence of Channel Thickness Variation on Temperature and Bias Induced Stress Instability of Amorphous SiInZnO Thin Film Transistors. <i>Transactions on Electrical and Electronic Materials</i> , 2017, 18, 51-54.	1.9	12
42	Effect of Annealing Temperature on the Electrical Performance of SiZnSnO Thin Film Transistors Fabricated by Radio Frequency Magnetron Sputtering. <i>Transactions on Electrical and Electronic Materials</i> , 2017, 18, 55-57.	1.9	2
43	Engineering of band gap states of amorphous SiZnSnO semiconductor as a function of Si doping concentration. <i>Scientific Reports</i> , 2016, 6, 36504.	3.3	40
44	Effect of Thermal Annealing on the Electrical Properties of In-Si-O/Ag/In-Si-O Multilayer. <i>Transactions on Electrical and Electronic Materials</i> , 2016, 17, 201-203.	1.9	3
45	Investigation of addition of silicon on the electrical properties of low temperature solution processed SiInZnO thin film transistor. <i>Journal of Sol-Gel Science and Technology</i> , 2015, 74, 482-487.	2.4	7
46	Role of metal capping layer on highly enhanced electrical performance of In-free Siâ€“Znâ€“Snâ€“O thin film transistor. <i>Thin Solid Films</i> , 2015, 594, 293-298.	1.8	28
47	High performance of full swing logic inverter using all n-types amorphous ZnSnO and SiZnSnO thin film transistors. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	36
48	Temperature Dependence of SiInZnO Thin Film Transistor Fabricated by Solution Process. <i>Transactions on Electrical and Electronic Materials</i> , 2015, 16, 46-48.	1.9	4
49	Investigation on Contact Resistance of Amorphous Indium Gallium Zinc Oxide Thin Film Transistors with Various Electrodes by Transmission Line Method. <i>Transactions on Electrical and Electronic Materials</i> , 2015, 16, 139-141.	1.9	9
50	Investigation on mechanism for instability under drain current stress in amorphous Siâ€“Inâ€“Znâ€“O thin-film transistors. <i>Thin Solid Films</i> , 2013, 527, 314-317.	1.8	5
51	Variation of optical and electrical properties of amorphous Inâ€“Gaâ€“Znâ€“O/Ag/amorphous Inâ€“Gaâ€“Znâ€“O depending on Ag thickness. <i>Thin Solid Films</i> , 2013, 536, 327-329.	1.8	13
52	First-principle study of amorphous SiZnSnO thin-film transistor with excellent stability. <i>Thin Solid Films</i> , 2013, 534, 609-613.	1.8	29
53	Full swing logic inverter with amorphous SiInZnO and GaInZnO thin film transistors. <i>Applied Physics Letters</i> , 2012, 101, 092103.	3.3	31
54	Influence of a highly doped buried layer for HfInZnO thin-film transistors. <i>Semiconductor Science and Technology</i> , 2012, 27, 012001.	2.0	19

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55	Role of Si as carrier suppressor in amorphous ZnSnO. Current Applied Physics, 2012, 12, S12-S16.	2.4	36
56	Effect of Trap Density on the Stability of SiInZnO Thin-Film Transistor under Temperature and Bias-Induced Stress. Electrochemical and Solid-State Letters, 2011, 14, H96.	2.2	22
57	Effect of interface states on the instability under temperature stress in amorphous SiInZnO thin film transistor. Applied Physics Letters, 2011, 99, 162101.	3.3	10
58	High stability of amorphous hafnium-indium-zinc-oxide thin film transistor. Applied Physics Letters, 2010, 96, .	3.3	122
59	Role of silicon in silicon-indium-zinc-oxide thin-film transistor. Applied Physics Letters, 2010, 97, .	3.3	51
60	Amorphous silicon-indium-zinc oxide semiconductor thin film transistors processed below 150°C. Applied Physics Letters, 2010, 97, .	3.3	86